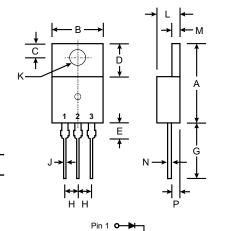


MBR1030CT - MBR1060CT

10A SCHOTTKY BARRIER RECTIFIER

Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- Plastic Material: UL Flammability Classification Rating 94V-0



TO-220AB							
Dim	Min	Max					
Α	14.22	15.88					
В	9.65	10.67					
С	2.54	3.43					
D	5.84	6.86					
E	_	6.35					
G	12.70	14.73					
Н	2.29	2.79					
J	0.51	1.14					
K	3.53∅	4.09∅					
L	3.56	4.83					
М	1.14	1.40					
N	0.30	0.64					
Р	2.03	2.92					
All Dimensions in mm							

Mechanical Data

Case: Molded Plastic

 Terminals: Plated Leads Solderable per MIL-STD-202, Method 208

Polarity: As Marked on Body
Weight: 2.24 grams (approx.)

Mounting Position: AnyMarking: Type Number

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	MBR 1030CT	MBR 1035CT	MBR 1040CT	MBR 1045CT	MBR 1050CT	MBR 1060CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	30	35	40	45	50	60	V
RMS Reverse Voltage	V _{R(RMS)}	21	24.5	28	31.5	35	42	V
Average Rectified Output Current (Note 1) @ T _C = 105°C	lo	10						Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)		125						А
Repetitive Peak Reverse Surge Current @ $t \le 2.0 \mu s$	I _{RRM}	1.0					Α	
Forward Voltage Drop	V_{FM}	0.57 0.70 0.70 0.80 0.84 0.95					80	V
		I _{RM} 0.1 15				mA		
Typical Junction Capacitance (Note 2)		150						pF
Typical Thermal Resistance Junction to Case (Note 1)		30						K/W
Voltage Rate of Change (Rated V _R)		1000						V/μs
Operating and Storage Temperature Range		-65 to +150						°C

Notes: 1. Thermal resistance junction to case mounted on heatsink.

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

